

METHOD FOR FABRICATING A SEMICONDUCTOR DEVICE HAVING IMPROVED HOT CARRIER IMMUNITY ABILITY

Abstract

The present invention discloses a method for fabricating a semiconductor device. A substrate is provided. At least one first and second gate structure, having sidewalls, are included on a surface of the substrate. A first ion implantation process is performed to form a shallow-junction doping region of a first conductive type in the substrate next to each of the sidewalls of the first gate structure, followed by the formation of offset spacers on each of the sidewalls of the first and second gate structure. A second ion implantation process is performed to form a shallow-junction doping region of a second conductive type in the substrate next to the offset spacer on each of the sidewalls of the second gate structure.